



CfXYf]b['-bZcf a Uh]cb'(Example)

DF9 : 9F98 'D#B'	D57 ?=B ; 7C89'	Auf_]b['	A=B=A I A' D57 ? 5 ; 9fidWgŁ	=BB9F'6CL' E I 5BH-HMfidWgŁ	C I H9F'75FHCB' E I 5BH-HMfidWgŁ	89@=J9FM'AC89
YJGD20G10BQ	F1	YJGD20G10B	5000	10000	100000	13" reel

BACGfi8]Y%#8]Y&Ł 9'YWhf]WU'' 7 \UfUWhYf]gh]Wg'(T_J=25 unless otherwise noted)

DUFU a YhYf'	Gm a Vc''	7 cbX]h]cbg'	A]b'	Hmd'	AUI'	I b]hg'
GhUh]W' DUFU a YhYf'						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	100			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V			1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ± 20V, V _{DS} =0V			± 100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	1.0	1.8	2.5	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D =20A		16	22	m
		V _{GS} = 4.5V, I _D =10A		18	27	
Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V		0.9	1.3	V
Gate Resistance	R _g	f=1MHz		1.5		
8mbU a]W' DUFU a YhYfg						
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1MHZ		1240		pF
Output Capacitance	C _{oss}			740		
Reverse Transfer Capacitance	C _{rss}			25		
Gk]hW\]b[' DUFU a YhYfg						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =50V, I _D =20A		17		nC
Gate-Source Charge	Q _{gs}			6		
Gate-Drain Charge	Q _{gd}			3		
Reverse Recovery Chrage	Q _{rr}	I _F =20A, di/dt=100A/us		42		
Reverse Recovery Time	t _{rr}			40		
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =50V, I _D =20A R _{GEN} =3.0		40		ns
Turn-on Rise Time	t _r			12		
Turn-off Delay Time	t _{D(off)}			55		
Turn-off fall Time	t _f			16		

- A. Repetitive rating; pulse width limited by max. junction temperature.
- B. V_{DD}=50V, R_G=25 , L=2mH, I_{AS}=9A.
- C. Pd is based on max. junction temperature, using junction-case thermal resistance.
- D. The value of R_{JA} is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with TA =25° C. The Power dissipation PDSM is based on R_{JA} t_{10s} and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.



'BACGf18]Y%#8]Y&l`Hmd]WU`DYfZcf a UbWY`7 \UfUWhYf]gh]Wg

ncO3 zh

nt

Figure1. Output Characteristics

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M> ; 8&\$; %\$6 E

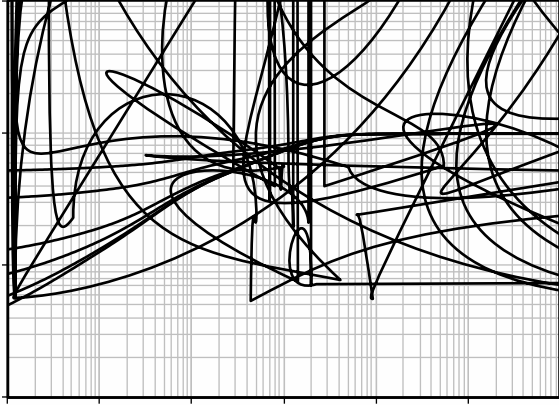


Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area

M> ; 8&\$; %\$6 E



8]gW'U]a Yf'

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